



## **GKI10194 Information**



For Reference Only

**Part Number** GKI10194 **Manufacturer** Sanken

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 100V 7A 8DFN

Package 8-PowerTDFN

For the pricing/inventory/lead time, please contact

us

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# **GKI10194 Specifications**

Manufacturer Part Number         GKI10194           Manufacturer         Sanken           Category         Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single           Package         8-PowerTDFN           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         100V           Current - Continuous Drain (Id) @ 25°C         7A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.5V @ 1mA           Gate Charge (Qg) (Max) @ Vgs         55.8nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         3990pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         3.1W (Ta), 77W (Tc)           Rds On (Max) @ Id, Vgs         17.6 mOhm @ 20.4A, 10V           Operating Temperature         150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         8-DFN (5x6)           Package / Case         8-PowerTDFN		
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  8-PowerTDFN  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  7A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vds  10put Capacitance (Ciss) (Max) @ Vds  10put	Manufacturer Part Number	GKI10194
Package         8-PowerTDFN           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         100V           Current - Continuous Drain (Id) @ 25°C         7A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.5V @ 1mA           Gate Charge (Qg) (Max) @ Vgs         55.8nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         3990pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         3.1W (Ta), 77W (Tc)           Rds On (Max) @ Id, Vgs         17.6 mOhm @ 20.4A, 10V           Operating Temperature         150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         8-DFN (5x6)           Package / Case         8-PowerTDFN	Manufacturer	Sanken
Package8-PowerTDFNSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C7A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.5V @ 1mAGate Charge (Qg) (Max) @ Vgs55.8nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3990pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)3.1W (Ta), 77W (Tc)Rds On (Max) @ Id, Vgs17.6 mOhm @ 20.4A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-DFN (5x6)Package / Case8-PowerTDFN	Category	Discrete Semiconductor Products
Series - Channel  FET Type N-Channel  Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  7A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  #20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  17.6 mOhm @ 20.4A, 10V  Operating Temperature  Mounting Type  Surface Mount  Supplier Device Package  Package / Case  NOSFET (Metal Oxide)  #0. Channel  #0. MOSFET (Metal Oxide)  #0. VGFT (Metal Oxid		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 7A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.5V @ ImA Gate Charge (Qg) (Max) @ Vgs 55.8nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3990pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.1W (Ta), 77W (Tc) Rds On (Max) @ Id, Vgs 17.6 mOhm @ 20.4A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-DFN (5x6) Package / Case 8-PowerTDFN	Package	8-PowerTDFN
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  7A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  **EUV**  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  17.6 mOhm @ 20.4A, 10V  Operating Temperature  Mounting Type  Surface Mount  Supplier Device Package  Package / Case  **MOSFET (Metal Oxide)  100V  7A (Ta)  7A (Ta)  7A (Ta)  7A (Ta)  7A (Ta)  7B (ToV  7B (Ta)  7TW (Tc)  150°C (TJ)  8B (Ta)  8-DFN (5x6)  8-PowerTDFN	Series	-
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  7A (Ta)  7brive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  17.6 mOhm @ 20.4A, 10V  Operating Temperature  Mounting Type  Surface Mount  Supplier Device Package  Package / Case  100V  7A (Ta)  7	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  17.6 mOhm @ 20.4A, 10V  Derating Temperature  Mounting Type  Surface Mount  Supplier Device Package Package / Case  7A (Ta)  7A (Ta	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  17.6 mOhm @ 20.4A, 10V  Derating Temperature  Mounting Type  Surface Mount  Supplier Device Package  Package / Case  4.5V, 10V  2.5V @ 1mA  3.990pF @ 25V  4.20V  55.8nC @ 10V  3990pF @ 25V  4.70V  4.7	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  55.8nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  3990pF @ 25V  Vgs (Max)  FET Feature  - Power Dissipation (Max)  3.1W (Ta), 77W (Tc)  Rds On (Max) @ Id, Vgs  17.6 mOhm @ 20.4A, 10V  Operating Temperature  150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  8-DFN (5x6)  Package / Case  8-PowerTDFN	Current - Continuous Drain (Id) @ 25°C	7A (Ta)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  17.6 mOhm @ 20.4A, 10V  Operating Temperature  Mounting Type  Surface Mount  Supplier Device Package  Package / Case  55.8nC @ 10V  3990pF @ 25V  ±20V  FET Feature  -  Nounting Type  Sufface Mount  Surface Mount  8-DFN (5x6)  8-PowerTDFN	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds  3990pF @ 25V  Vgs (Max)  ET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  17.6 mOhm @ 20.4A, 10V  Operating Temperature  150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  8-DFN (5x6)  Package / Case  8-PowerTDFN	Vgs(th) (Max) @ Id	2.5V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)3.1W (Ta), 77W (Tc)Rds On (Max) @ Id, Vgs17.6 mOhm @ 20.4A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-DFN (5x6)Package / Case8-PowerTDFN	Gate Charge (Qg) (Max) @ Vgs	55.8nC @ 10V
FET Feature - Power Dissipation (Max) 3.1W (Ta), 77W (Tc) Rds On (Max) @ Id, Vgs 17.6 mOhm @ 20.4A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-DFN (5x6) Package / Case 8-PowerTDFN	Input Capacitance (Ciss) (Max) @ Vds	3990pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  17.6 mOhm @ 20.4A, 10V  Operating Temperature  150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  8-DFN (5x6)  Package / Case  8-PowerTDFN	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs17.6 mOhm @ 20.4A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-DFN (5x6)Package / Case8-PowerTDFN	FET Feature	-
Operating Temperature 150°C (TJ)  Mounting Type Surface Mount  Supplier Device Package 8-DFN (5x6)  Package / Case 8-PowerTDFN	Power Dissipation (Max)	3.1W (Ta), 77W (Tc)
Mounting Type Surface Mount Supplier Device Package 8-DFN (5x6) Package / Case 8-PowerTDFN	Rds On (Max) @ Id, Vgs	17.6 mOhm @ 20.4A, 10V
Supplier Device Package 8-DFN (5x6) Package / Case 8-PowerTDFN	Operating Temperature	150°C (TJ)
Package / Case 8-PowerTDFN	Mounting Type	Surface Mount
	Supplier Device Package	8-DFN (5x6)
Report errors?	Package / Case	8-PowerTDFN
		Report errors?

### **GKI10194 Guarantees**



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **GKI10194 Payment Methods**



















## **GKI10194 Shipping Methods**













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